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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

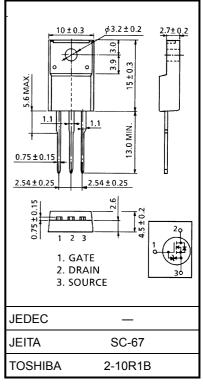
2SK2679

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance $: R_{DS} (ON) = 0.84 \Omega (typ.)$
- High forward transfer admittance $|Y_{fs}| = 4.4 \text{ S}$ (typ.)
- $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 400 \ V)$ Low leakage current
- Enhancement-mode : $V_{th} = 2.0 \sim 4.0 V (V_{DS} = 10 V, I_D = 1 mA)$

Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit
Drain-source voltage		V _{DSS}	400	V
Drain-gate voltage (R	_{GS} = 20 kΩ)	V _{DGR}	400	V
Gate-source voltage		V _{GSS}	±30	V
Drain current	DC (Note 1)	I _D	5.5	А
	Pulse (Note 1)	I _{DP}	22	А
Drain power dissipation	n (Tc = 25°C)	PD	35	W
Single pulse avalanche	e energy (Note 2)	E _{AS}	223	mJ
Avalanche current		I _{AR}	5.5	А
Repetitive avalanche e	energy (Note 3)	E _{AR}	3.5	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature ra	ange	T _{stg}	-55~150	°C



Weight: 1.9 g (typ.)

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch−c)}	3.57	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	62.5	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 12 mH, R_G = 25 Ω , I_{AR} = 5.5 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

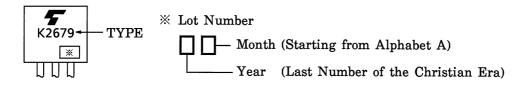
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V		_	±10	μA
Gate-source bre	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 400 V, V _{GS} = 0 V		_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	400	_	_	V
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 3 A		0.84	1.2	Ω
Forward transfer	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3 A	2.0	4.4	_	S
Input capacitance	e	C _{iss}			720	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		80	_	pF
Output capacitance		Coss	1		250	_	
Switching time	Rise time	tr	$V_{\text{GS}} \stackrel{10V}{}_{0V} \stackrel{I_{\text{D}}=2A}{}_{\circ} V_{\text{out}}$ $R_{\text{L}}=100\Omega$ $V_{\text{DD}} \stackrel{=}{=} 200V$	_	15	_	
	Turn-on time	t _{on}		_	30	_	20
	Fall time	t _f		_	25	_	ns
	Turn-off time	t _{off}	Duty $\leq 1\%$, t _w =10µs	_	110	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	17	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 320 V, V _{GS} = 10 V, I _D = 5.5 A -		10	_	nC
Gate-drain ("miller") Charge		Q _{gd}			7	_	

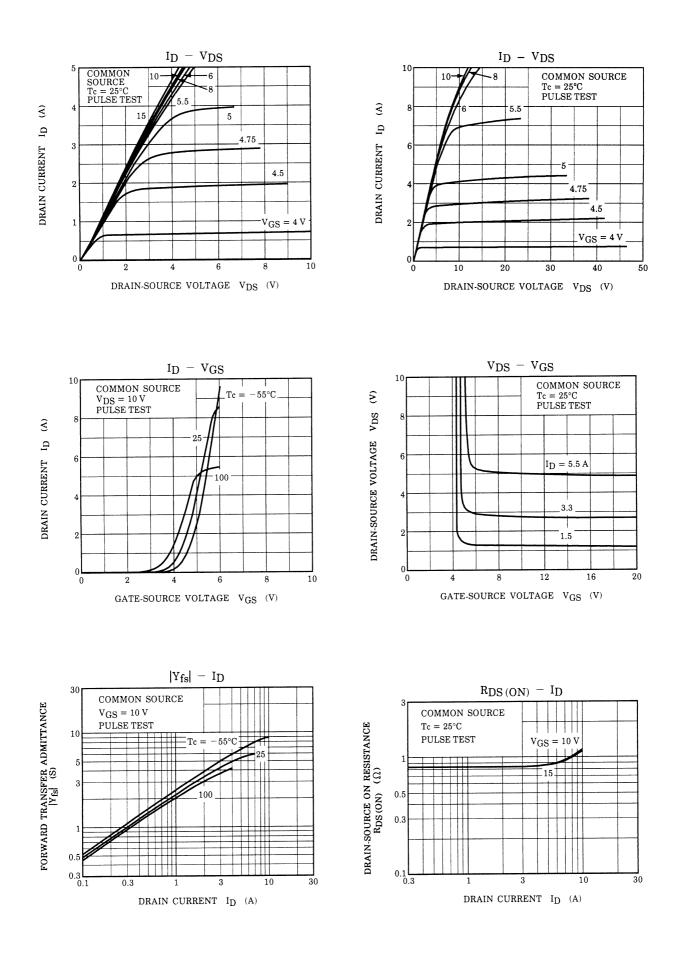
Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	5.5	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	22	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 5.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 5.5 A, V _{GS} = 0 V		350		ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 Å / μs	_	2.1	_	μC

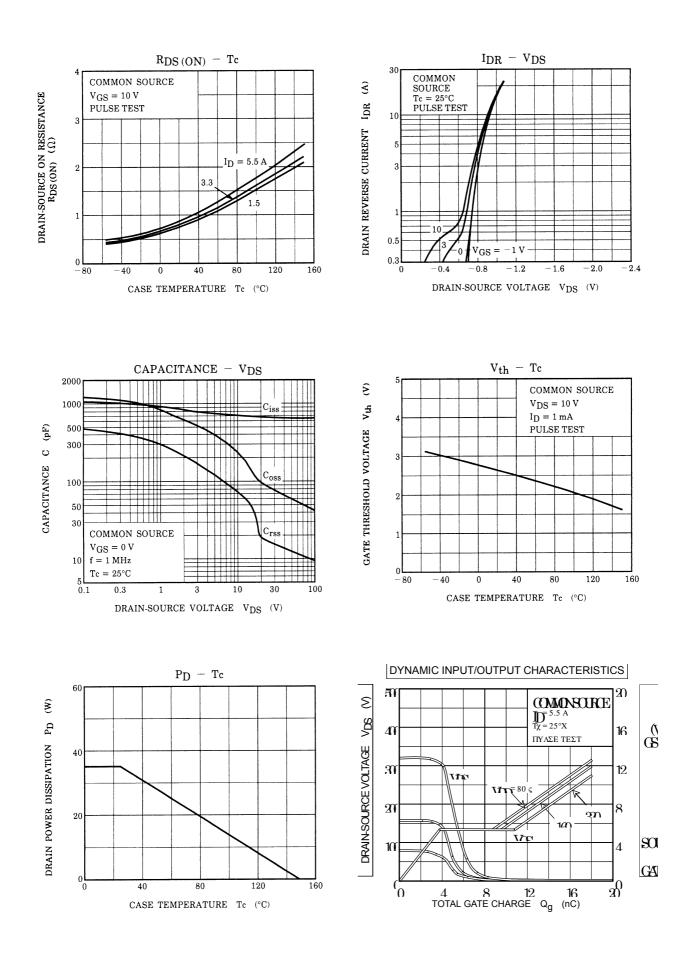
Marking

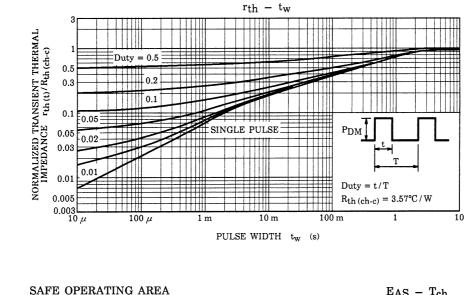


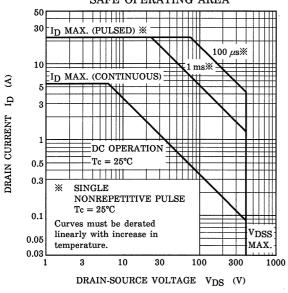
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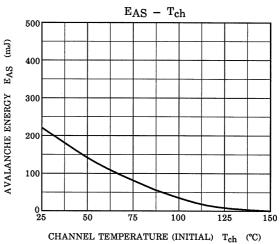


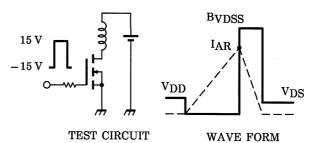
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 $\begin{array}{l} \mathrm{RG} = 25 \ \Omega \\ \mathrm{VDD} = 90 \ \mathrm{V}, \ \mathrm{L} = 12 \ \mathrm{mH} \end{array} \qquad \qquad \mathrm{EAS} = \frac{1}{2} \cdot \mathrm{L} \cdot \mathrm{I}^2 \cdot \left(\frac{\mathrm{BVDSS}}{\mathrm{BVDSS} - \mathrm{VDD}} \right) \end{array}$

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